

# Tie Lin

## List of Publications by Year in descending order

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97  
papers

3,302  
citations

186254

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h-index

149686

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all docs

99  
docs citations

99  
times ranked

4396  
citing authors

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 1  | Epitaxial growth and phase evolution of ferroelectric La-doped HfO <sub>2</sub> films. Applied Physics Letters, 2022, 120, .   | 3.3  | 7         |
| 2  | HgCdTe/black phosphorus van der Waals heterojunction for high-performance polarization-sensitive midwave infrared photodetector. Science Advances, 2022, 8, eabn1811.                          | 10.3 | 50        |
| 3  | End-Bonded Contacts of Tellurium Transistors. ACS Applied Materials & Interfaces, 2021, 13, 7766-7772.   | 8.0  | 12        |
| 4  | Gate-tunable Photodiodes Based on Mixed-dimensional Te/MoTe <sub>2</sub> Van der Waals Heterojunctions. Advanced Electronic Materials, 2021, 7, 2001066.                                       | 5.1  | 29        |
| 5  | Interface engineering of ferroelectric-gated MoS <sub>2</sub> phototransistor. Science China Information Sciences, 2021, 64, 1.  | 4.3  | 10        |
| 6  | Ferroelectric-tuned van der Waals heterojunction with band alignment evolution. Nature Communications, 2021, 12, 4030.   | 12.8 | 79        |
| 7  | Functionalities enhancement by an anisotropic strain competition. Ferroelectrics, 2021, 583, 264-277.  | 0.6  | 0         |
| 8  | Ultrasensitive negative capacitance phototransistors. Nature Communications, 2020, 11, 101.  | 12.8 | 124       |
| 9  | Highly Sensitive InSb Nanosheets Infrared Photodetector Passivated by Ferroelectric Polymer. Advanced Functional Materials, 2020, 30, 2006156.   | 14.9 | 41        |
| 10 | A versatile photodetector assisted by photovoltaic and bolometric effects. Light: Science and Applications, 2020, 9, 160.  | 16.6 | 56        |
| 11 | MoTe <sub>2</sub> p-n Homojunctions Defined by Ferroelectric Polarization. Advanced Materials, 2020, 32, e1907937.   | 21.0 | 115       |
| 12 | Two-dimensional series connected photovoltaic cells defined by ferroelectric domains. Applied Physics Letters, 2020, 116, .  | 3.3  | 10        |
| 13 | Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. Nature Electronics, 2020, 3, 43-50.  | 26.0 | 167       |
| 14 | Extremely Low Dark Current MoS <sub>2</sub> Photodetector via 2D Halide Perovskite as the Electron Reservoir. Advanced Optical Materials, 2020, 8, 1901402.                                    | 7.3  | 55        |
| 15 | Multifunctional MoS <sub>2</sub> Transistors with Electrolyte Gel Gating. Small, 2020, 16, e2000420.   | 10.0 | 23        |
| 16 | Ultrabroad-Spectrum Photodetectors: Multimechanism Synergistic Photodetectors with Ultrabroad Spectrum Response from 375 nm to 10 Åµm (Adv. Sci. 15/2019). Advanced Science, 2019, 6, 1970089. | 11.2 | 2         |
| 17 | Ferroelectric properties of gradient doped Y <sub>2</sub> O <sub>3</sub> :HfO <sub>2</sub> thin films grown by pulsed laser deposition. Applied Physics Letters, 2019, 115, .                  | 3.3  | 9         |
| 18 | A study on ionic gated MoS <sub>2</sub> phototransistors. Science China Information Sciences, 2019, 62, 1.   | 4.3  | 8         |

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|----|---|------|-----------|
| 19 | A gate-free MoS <sub>2</sub> phototransistor assisted by ferroelectrics. Journal of Semiconductors, 2019, 40, 092002.   | 3.7  | 10        |
| 20 | Multimode Signal Processor Unit Based on the Ambipolar WSe <sub>2</sub> /Cr Schottky Junction. ACS Applied Materials & Interfaces, 2019, 11, 38895-38901.   | 8.0  | 3         |
| 21 | Magnetotransport property of graded AlGaIn/GaN heterostructure. Superlattices and Microstructures, 2019, 135, 106262.   | 3.1  | 3         |
| 22 | Ultrasensitive Hybrid MoS <sub>2</sub> /ZnCdSe Quantum Dot Photodetectors with High Gain. ACS Applied Materials & Interfaces, 2019, 11, 23667-23672.  | 8.0  | 62        |
| 23 | Large-area high quality PtSe <sub>2</sub> thin film with versatile polarity. Information Materials, 2019, 1, 260-267.   | 17.3 | 54        |
| 24 | A Robust Artificial Synapse Based on Organic Ferroelectric Polymer. Advanced Electronic Materials, 2019, 5, 1800600.  | 5.1  | 129       |
| 25 | Ferroelectric Synapses: A Robust Artificial Synapse Based on Organic Ferroelectric Polymer (Adv.) Tj ETQq1 1 0.784314 rgBT (Overlock 3  | 5.1  | 3         |
| 26 | Structural, electrical and magnetic properties of (110)-oriented BF-BZT-ST Films. Ceramics International, 2018, 44, 9053-9057.  | 4.8  | 2         |
| 27 | Optoelectronics: High-performance Photovoltaic Detector Based on MoTe <sub>2</sub> /MoS <sub>2</sub> Van der Waals Heterostructure (Small 9/2018). Small, 2018, 14, 1870038.                      | 10.0 | 7         |
| 28 | High-performance Photovoltaic Detector Based on MoTe <sub>2</sub> /MoS <sub>2</sub> Van der Waals Heterostructure. Small, 2018, 14, 1703293.  | 10.0 | 205       |
| 29 | Mechanism and application method to analyze the carrier scattering factor by electrical conductivity ratio based on thermoelectric property measurement. Journal of Applied Physics, 2018, 123, . | 2.5  | 13        |
| 30 | High-performance lead-free two-dimensional perovskite photo transistors assisted by ferroelectric dielectrics. Journal of Materials Chemistry C, 2018, 6, 12714-12720.                            | 5.5  | 39        |
| 31 | Ferroelectric FET for nonvolatile memory application with two-dimensional MoSe <sub>2</sub> channels. 2D Materials, 2017, 4, 025036.  | 4.4  | 85        |
| 32 | Photoexcited terahertz conductivity dynamics of graphene tuned by oxygen-adsorption. Applied Physics Letters, 2017, 110, .  | 3.3  | 22        |
| 33 | Optical Manipulation of Rashba Spin-Orbit Coupling at SrTiO <sub>3</sub> -Based Oxide Interfaces. Nano Letters, 2017, 17, 6534-6539.  | 9.1  | 30        |
| 34 | Two-dimensional negative capacitance transistor with polyvinylidene fluoride-based ferroelectric polymer gating. Npj 2D Materials and Applications, 2017, 1, .                                    | 7.9  | 77        |
| 35 | Electrical characterization of MoS <sub>2</sub> field-effect transistors with different dielectric polymer gate. AIP Advances, 2017, 7, .   | 1.3  | 15        |
| 36 | Strained HgTe plates grown on SrTiO <sub>3</sub> investigated by micro-Raman mapping. Journal of Applied Physics, 2016, 120, 115304.  | 2.5  | 4         |

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|----|--|------|-----------|
| 37 | Ferroelectric polymer tuned two dimensional layered MoTe <sub>2</sub> photodetector. RSC Advances, 2016, 6, 87416-87421.   | 3.6  | 51        |
| 38 | Highly sensitive visible to infrared MoTe <sub>2</sub> photodetectors enhanced by the photogating effect. Nanotechnology, 2016, 27, 445201.  | 2.6  | 188       |
| 39 | Single crystal investigated by infrared  |      |           |
| 40 | Visible to short wavelength infrared In <sub>2</sub> Se <sub>3</sub> -nanoflake photodetector gated by a ferroelectric polymer. Nanotechnology, 2016, 27, 364002.  | 2.6  | 63        |
| 41 | Spin-glass state induced low field magnetization-step effect in a Hg <sub>1-x</sub> Mn <sub>x</sub> Te single crystal. Physica Status Solidi (B): Basic Research, 2016, 253, 2015-2019.  | 1.5  | 0         |
| 42 | Tunnel electroresistance through organic ferroelectrics. Nature Communications, 2016, 7, 11502.  | 12.8 | 104       |
| 43 | BES-III distributed computing status. Physics of Particles and Nuclei Letters, 2016, 13, 700-703.  | 0.4  | 0         |
| 44 | Flexible graphene field effect transistor with ferroelectric polymer gate. Optical and Quantum Electronics, 2016, 48, 1.   | 3.3  | 21        |
| 45 | Photodetectors: Ultrasensitive and Broadband MoS <sub>2</sub> Photodetector Driven by Ferroelectrics (Adv. Mater. 42/2015). Advanced Materials, 2015, 27, 6538-6538.   | 21.0 | 8         |
| 46 | Highly sensitive phototransistor based on GaSe nanosheets. Applied Physics Letters, 2015, 107, .   | 3.3  | 69        |
| 47 | Influence of local magnetization on acceptor-bound complex state in Hg <sub>1-x</sub> Mn <sub>x</sub> Te single crystals. Journal of Applied Physics, 2015, 118, 045707.   | 2.5  | 4         |
| 48 | Ultrasensitive and Broadband MoS <sub>2</sub> Photodetector Driven by Ferroelectrics. Advanced Materials, 2015, 27, 6575-6581.   | 21.0 | 722       |
| 49 | Properties of Tunability and Stored Energy Density in the Ferroelectric Multilayers. Ferroelectrics, 2015, 488, 112-118.   | 0.6  | 0         |
| 50 | Ferroelectric control of magnetism in P(VDF-TrFE)/Co heterostructure. Journal of Materials Science: Materials in Electronics, 2015, 26, 7502-7506.   | 2.2  | 9         |
| 51 | Long phase coherence length and anisotropic magnetoresistance in MgZnO thin film. Journal of Applied Physics, 2015, 117, .   | 2.5  | 5         |
| 52 | Effects of GaN interlayer on the transport properties of lattice-matched AlInN/AlN/GaN heterostructures. Journal of Applied Physics, 2015, 117, .  | 2.5  | 8         |
| 53 | Pyromellitic Diimide-Benzodithiophene Copolymer for Polymer Solar Cells: Effect of Side Chain Length and Thiophene $\pi$ -Bridge on Optical and Electronic Properties. Molecular Crystals and Liquid Crystals, 2014, 604, 151-163. | 0.9  | 2         |
| 54 | Design and synthesis of pyromellitic diimide-based donor-acceptor conjugated polymers for photovoltaic application. Polymers for Advanced Technologies, 2014, 25, 809-815.   | 3.2  | 1         |

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|----|--|-----|-----------|
| 55 | The nonlinear Rashba effect in Hg <sub>0.77</sub> Cd <sub>0.23</sub> Te inversion layers probed by weak antilocalization analysis. Journal of Applied Physics, 2013, 113, .  | 2.5 | 11        |
| 56 | The Cr-substitution concentration dependence of the structural, electric and magnetic behaviors for Aurivillius Bi <sub>5</sub> Ti <sub>3</sub> FeO <sub>15</sub> multiferroic ceramics. Journal of Applied Physics, 2013, 114, .            | 2.5 | 41        |
| 57 | The effective g-factor in In <sub>0.53</sub> Ga <sub>0.47</sub> As/In <sub>0.52</sub> Al <sub>0.48</sub> As quantum well investigated by magnetotransport measurement. Journal of Applied Physics, 2013, 113, 033704.                        | 2.5 | 3         |
| 58 | Microwave-enhanced dephasing time in a HgCdTe film. Applied Physics Letters, 2013, 102, 012108.  | 3.3 | 3         |
| 59 | Photoionization absorption and zero-field spin splitting of acceptor-bound magnetic polaron in p-type Hg <sub>1-x</sub> MnxTe single crystals. Journal of Applied Physics, 2012, 111, 083502.  | 2.5 | 5         |
| 60 | Effects of scattering on two-dimensional electron gases in InGaAs/InAlAs quantum wells. Journal of Applied Physics, 2012, 112, .   | 2.5 | 2         |
| 61 | Dielectric responses and scaling behaviors in Aurivillius Bi <sub>6</sub> Ti <sub>3</sub> Fe <sub>2</sub> O <sub>18</sub> multiferroic thin films. Applied Physics Letters, 2012, 100, .   | 3.3 | 75        |
| 62 | Competing conduction mechanisms of two-dimensional electrons and bulk-like electrons in the n-type surface of the naturally oxidized p-type HgCdTe thin film. Applied Physics A: Materials Science and Processing, 2012, 106, 703-707.       | 2.3 | 0         |
| 63 | Spin dependence of electron effective masses in InGaAs/InAlAs quantum well. Journal of Applied Physics, 2011, 110, 063707.   | 2.5 | 4         |
| 64 | Aging-induced abnormality of dielectric response under dc bias in Ba(Zr, Ti)O <sub>3</sub> thin films. Applied Physics A: Materials Science and Processing, 2011, 104, 123-128.  | 2.3 | 14        |
| 65 | Weak antilocalization effect in high-mobility two-dimensional electron gas in an inversion layer on p-type HgCdTe. Applied Physics Letters, 2011, 99, .  | 3.3 | 9         |
| 66 | Magnetotransport properties of (In,Zn)As/InAs p-n junctions. Applied Physics Letters, 2011, 98, 142110.  | 3.3 | 1         |
| 67 | Anomalous shift of the beating nodes in illumination-controlled $\ln_{1-x}\text{In}_x\text{As}$ quantum wells. Physical Review B, 2010, 81, .  | 3.2 | 3         |
| 68 | Insulator-quantum Hall conductor transition in high electron density gated InGaAs/InAlAs quantum wells. Journal of Applied Physics, 2010, 108, 063701.   | 2.5 | 8         |
| 69 | Magnetic Field Induced Dielectric and Ferroelectric Behaviors in Pb(Zr <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> /CoFe <sub>2</sub> O <sub>4</sub> -3 Thick Composite Films. Ferroelectrics, 2010, 410, 50-58.                        | 0.6 | 2         |
| 70 | STRUCTURES AND PROPERTIES OF PZT(52/48) THIN FILMS WITH DIFFERENT SUBSTRATE TEMPERATURE AND OXYGEN PERCENTAGE IN MIXED Ar AND O <sub>2</sub> GAS ON LNO/Si (100) BY SPUTTERING. Integrated Ferroelectrics, 2010, 113, 63-71.                 | 0.7 | 1         |
| 71 | EFFECT OF SPUTTERING WORKING PRESSURE ON MICROSTRUCTURES AND PROPERTIES OF PZT THIN FILMS. Integrated Ferroelectrics, 2010, 113, 31-40.  | 0.7 | 3         |
| 72 | Experimental approaches to zero-field spin splitting in a gated high-mobility In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP quantum well structure: Weak antilocalization and beating pattern. Journal of Applied Physics, 2010, 107, 053708. | 2.5 | 4         |

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|----|--|-----|-----------|
| 73 | Temperature dependent transport properties of p-Pb <sub>1-x</sub> MnxSe films. Journal of Applied Physics, 2010, 108, .  | 2.5 | 4         |
| 74 | Transport properties of a spin-split two-dimensional electron gas in an In <sub>0.53</sub> Ga <sub>0.47</sub> As <sup>+</sup> InP quantum well structure. Journal of Applied Physics, 2009, 106, 073722.   | 2.5 | 5         |
| 75 | Transport properties of AlGaAs/GaAs parabolic quantum wells. Journal of Applied Physics, 2009, 105, .  | 2.5 | 21        |
| 76 | Fabrication and characteristics of porous germanium films. Science and Technology of Advanced Materials, 2009, 10, 065001.   | 6.1 | 30        |
| 77 | Influence of the illumination on the subband structure and occupation in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures. Applied Physics A: Materials Science and Processing, 2009, 96, 953-957.                                       | 2.3 | 1         |
| 78 | Effect of Fe-doping concentration on microstructure, electrical, and magnetic properties of Pb(Zr <sub>0.5</sub> Ti <sub>0.5</sub> )O <sub>3</sub> thin films prepared by chemical solution deposition. Journal of Applied Physics, 2009, 106, . | 2.5 | 26        |
| 79 | Magnetoresistance in high-density two-dimensional electron gas confined in InAlAs/InGaAs quantum well. Applied Physics Letters, 2009, 94, 152107.  | 3.3 | 5         |
| 80 | Influence of the illumination on the spin splitting of the two-dimensional electron gas in Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN heterostructures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2339-2341.         | 0.8 | 0         |
| 81 | Weak antilocalization and beating pattern in high electron mobility Al <sub>x</sub> Ga <sub>1-x</sub> N/GaN two-dimensional electron gas with strong Rashba spin-orbit coupling. Journal of Applied Physics, 2008, 104, 053703.                  | 2.5 | 16        |
| 82 | The alternative route of low-temperature preparation of highly oriented lead zirconate titanate thin films by high gas-pressure processing. Journal of Materials Research, 2008, 23, 2846-2853.  | 2.6 | 9         |
| 83 | Hopping conduction and low-frequency dielectric relaxation in 5mol% Mn doped (Pb,Sr)TiO <sub>3</sub> films. Journal of Applied Physics, 2008, 104, .   | 2.5 | 47        |
| 84 | Low-temperature dielectric properties of Langmuir-Blodgett ferroelectric polymer films. Journal of Applied Physics, 2008, 103, 034110.   | 2.5 | 12        |
| 85 | Electric field induced conversion in the nature of the phase transition from the first order to the second order for Langmuir-Boldgett polymer films. Applied Physics Letters, 2007, 91, .   | 3.3 | 9         |
| 86 | Structural and optical properties of Bi <sub>3.25</sub> Nd <sub>0.75</sub> Ti <sub>3</sub> O <sub>12</sub> ferroelectric thin films. Applied Physics A: Materials Science and Processing, 2007, 88, 439-442.                                     | 2.3 | 3         |
| 87 | Infrared Optical Properties of Bi <sub>4-x</sub> NdxTi <sub>3</sub> O <sub>12</sub> Thin Films Prepared by a Chemical Solution Method. , 2006, , .   |     | 0         |
| 88 | LOW-TEMPERATURE PREPARATION OF Pb(ZrxTi <sub>1-x</sub> )O <sub>3</sub> THIN FILM. Integrated Ferroelectrics, 2006, 81, 123-128.  | 0.7 | 3         |
| 89 | LEAKAGE CURRENT MECHANISMS OF SrTiO <sub>3</sub> THIN FILMS WITH MIS STRUCTURES. Integrated Ferroelectrics, 2005, 74, 189-197.   | 0.7 | 4         |
| 90 | Retention characteristics of Au/Bi <sub>3.25</sub> La <sub>0.75</sub> Ti <sub>3</sub> O <sub>12</sub> /Si metal-ferro- electric-semiconductor structure. Applied Physics A: Materials Science and Processing, 2005, 81, 389-392.                 | 2.3 | 2         |

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|----|--|-----|-----------|
| 91 | Effect of LaNiO <sub>3</sub> buffer layers on the structure and electrical properties of sol-gel-derived Pb(Mg <sub>1/3</sub> Nb <sub>2/3</sub> )O <sub>3</sub> PbTiO <sub>3</sub> thin films. Applied Physics A: Materials Science and Processing, 2005, 81, 1025-1028. | 2.3 | 15        |
| 92 | Low-temperature preparation of highly (100)-oriented Pb(Zr <sub>x</sub> Ti <sub>1-x</sub> )O <sub>3</sub> thin film by high oxygen-pressure processing. Applied Physics Letters, 2005, 86, 252902.   | 3.3 | 33        |
| 93 | Infrared optical properties of PbZr <sub>0.4</sub> Ti <sub>0.6</sub> O <sub>3</sub> /La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> heterostructures on platinized silicon substrate. Applied Physics A: Materials Science and Processing, 2004, 78, 119-123.      | 2.3 | 2         |
| 94 | Effect of substitution of vanadium on the structure and electrical properties of Bi <sub>3.25</sub> La <sub>0.75</sub> Ti <sub>3</sub> O <sub>12</sub> thin films. Applied Physics A: Materials Science and Processing, 2004, 78, 1089-1091.                             | 2.3 | 8         |
| 95 | Temperature dependence of ferroelectric and dielectric properties of PbZr <sub>0.5</sub> Ti <sub>0.5</sub> O <sub>3</sub> thin film based capacitors. Applied Physics Letters, 2002, 81, 4035-4037.  | 3.3 | 28        |
| 96 | Influence of doping position on subband properties in In <sub>0.2</sub> Ga <sub>0.8</sub> As/GaAs heterostructures. Physical Review B, 2002, 65, .   | 3.2 | 9         |
| 97 | Infrared optical properties of lanthanum strontium cobalt thin films. , 0, , .   |     | 0         |